

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2155	(438/18,108,763).CCLS.	USPAT; USOCR	OR	OFF	2005/07/25 11:37
S2	3	((("6162652") or ("6143668") or ("6291268")).PN.	USPAT; USOCR	OR	OFF	2005/07/25 13:33
S3	3314	(438/14,18,108,763).CCLS.	USPAT; USOCR	OR	OFF	2005/07/25 11:37
S4	3314	(438/14,18,108,763).CCLS.	USPAT; USOCR	OR	OFF	2005/07/25 13:34
S5	95	"I4" and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 13:38
S6	650	S4 and (sputtering or ion adj milling)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 13:41
S7	48	"L8" and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 13:54
S8	132	S6 and (semiconductor and cleaning)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 13:54
S9	131	S8 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 13:55
S10	58	S9 and (argon or Ar or helium or He or neon or Ne)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 15:15

S11	7561	wafer near cleaning	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 15:15
S12	877	S11 and (sputtering or ion adj milling)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 15:22
S13	806	S12 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 15:18
S14	463	S13 and (argon or Ar or helium or He or neon or Ne)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 15:19
S15	74	S14 and testing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 10:52
S16	24	S14 and (contamina\$4 near removal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 15:24
S17	10112	((134/1.1,1.2,1.3) or (324/754,756, 757,765)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/26 11:02
S18	9530	S17 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/26 11:06

S20	2054	S18 and (metal\$3 or tin or Sn or aluminum or copper) same (clean\$3 or remove\$3 or etch\$3 or sputter\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/27 08:47
S21	577	S20 and (argon or Ar or helium or He or neon or Ne)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/26 11:21
S22	483	S21 and (pad or bump or layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/26 11:22
S23	202	S22 and (prob\$3) and (test\$3 or measur\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/26 11:24
S24	193	S23 and (semiconductor or silicon or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/26 11:25
S27	1103822	(metal\$3 or tin or Sn or aluminum or copper) same (clean\$3 or remove\$3 or etch\$3 or sputter\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 08:49
S28	632432	S27 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 08:50
S29	180701	S28 and (semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 16:03

S30	4590	S29 and (metal near (pads or bumps))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 08:53
S31	834	S30 and (cleaning)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 08:55
S32	606	S31 and (prob\$3 or test\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 09:28
S33	87	S32 and (sputtering and (noble adj gas\$2 or (argon or Ar or helium or He or neon or Ne)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 09:27
S34	387	S32 and (tin or Sn or tin adj alloy)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 09:55
S35	432	S31 and (sputter\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28:10:14
S36	1103822	(metal\$3 or tin or Sn or aluminum or copper) same (clean\$3 or remove\$3 or etch\$3 or sputter\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 16:04
S37	632432	S36 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 16:04

S38	14249	S37 and (cleaning and (testing or probing))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 16:06
S39	278	S38 and (semiconductor and (metal near (pad or bump)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 16:08
S40	214	S39 and (tin or Sn or Sn adj alloy or tin adj alloy)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 16:09
S41	1104516	(metal\$3 or tin or Sn or aluminum or copper) same (clean\$3 or remove\$3 or etch\$3 or sputter\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 10:14
S42	632563	S41 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 10:14
S43	180755	S42 and (semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 10:14
S44	4591	S43 and (metal near (pads or bumps))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 10:14
S45	834	S44 and (cleaning)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 10:14

S46	432	S45 and (sputter\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 10:14
S47	147	S46 and (noble adj gas\$2 or (argon or Ar or helium or He or neon or Ne))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 10:22
S48	33	S47 and (sputter\$3 near clean\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 10:23
S49	7573	wafer near cleaning	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 10:55
S50	879	S49 and (sputtering or ion adj milling)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 10:55
S51	807	S50 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 10:55
S52	464	S51 and (argon or Ar or helium or He or neon or Ne)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 10:55
S53	91	S52 and (argon or Ar) and (helium or He) and (neon or NE)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/28 10:56